

AMENDMENTS

In the Claims:

Please amend claim 8 as follows:

Q1 8. (Amended) A method for producing a nitride compound semiconductor light emitting device, wherein a semiconductor multilayer structure including an active layer of a quantum well structure made by a nitride compound semiconductor and an acceptor doping layer is integrated on a GaN substrate having a crystal orientation which is tilted away from a <0001> direction by an angle which is equal to or greater than about 0.05° and which is equal to or less than about 2°, the active layer including at least one barrier layer and at least one well layer, the method comprising the steps of:

stopping the growth of the active layer for a certain period of time after forming the well layer of the active layer including the at least one barrier layer and at least one well layer; and

stopping the growth of the nitride compound semiconductor for a certain period of time after forming the nitride compound semiconductor which contacts with the well layer and becomes the barrier layer having band-gap energy larger than that of the well layer.

9. A method according to claim 8, wherein the predetermined length of a wait period is equal to or greater than about 1 second and is equal to or less than about 60 minutes.

10. A method according to claim 8, further comprising:
supplying a carrier gas into the chamber, in which the GaN substrate is placed, during a wait period after at least one of the at least one well layer and the at least one barrier layer has been formed, the carrier gas comprising nitrogen as a main component.

11. A method according to claim 8, further comprising:

A supplying a carrier gas and a group V gas into a chamber, in which the GaN substrate is placed, during a wait period after at least one of the at least one well layer and the at least one barrier layer has been formed, the carrier gas comprising nitrogen as a main component.
